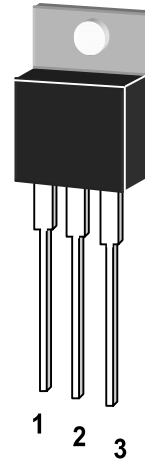


SD13003T

NPN Silicon Epitaxial Planar Transistor for power switching and electron rectifier applications.

The transistor is subdivided into one group according to its DC current gain.

On special request, these transistors can be manufactured in different pin configurations.



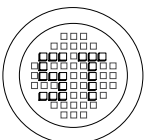
1. Base 2. Collector 3. Emitter

TO-220 Plastic Package

Absolute Maximum Ratings ($T_a = 25^\circ\text{C}$)

	Symbol	Rating	Unit
Collector Base Voltage	V_{CBO}	600	V
Collector Emitter Voltage	V_{CEO}	400	V
Emitter Base Voltage	V_{EBO}	9	V
Collector Current	I_{C}	1.5	A
Power Dissipation	P_{tot}	1.5	W
Junction Temperature	T_{j}	150	$^\circ\text{C}$
Storage Temperature Range	T_{s}	-55 to +150	$^\circ\text{C}$

G S P FORM A IS AVAILABLE



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РАДИОТЕХ-ТРЕЙД

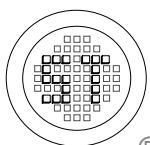
Тел.: (495) 795-0805
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Эл. почта: info@rct.ru
Веб: www.rct.ru

SD13003T

Characteristics at $T_{amb}=25\text{ }^{\circ}\text{C}$

	Symbol	Min.	Typ.	Max.	Unit
DC Current Gain at $V_{CE}=10\text{V}$, $I_C=100\text{mA}$	h_{FE}	10	-	70	
Collector Base Breakdown Voltage at $I_C=1\text{mA}$	$V_{(BR)CBO}$	600	-	-	V
Collector Emitter Breakdown Voltage at $I_C=10\text{mA}$	$V_{(BR)CEO}$	400	-	-	V
Emitter Base Breakdown Voltage at $I_E=1\text{mA}$	$V_{(BR)EBO}$	9	-	-	V
Collector Cutoff Current at $V_{CB}=600\text{V}$	I_{CBO}	-	-	100	nA
Emitter Cutoff Current at $V_{EB}=9\text{V}$	I_{EBO}	-	-	100	μA
Collector Emitter Saturation Voltage at $I_C=1\text{A}$, $I_B=250\text{mA}$	$V_{CE(sat)}$	-	-	1.0	V
Base-Emitter Saturation Voltage at $I_C=1\text{A}$, $I_B=250\text{mA}$	$V_{BE(sat)}$	-	-	1.2	V

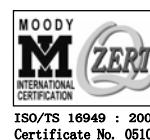
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SEMTECH ELECTRONICS LTD.

(Subsidiary of Semtech International Holdings Limited, a company listed on the Hong Kong Stock Exchange, Stock Code: 724)



Dated : 07/12/2002